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Zn-related deep centers in wurtzite GaN

Fabio Bernardini,[1] Vincenzo Fiorentini,[1] and R. M. Nieminen[2]

(1) Istituto Nazionale di Fisica della Materia – Dip. Scienze Fisiche, Università di Cagliari, Italy
(2) Laboratory of Physics, Helsinki University of Technology, FIN-02150 Espoo, Finland

Zn in GaN forms an efficient radiative center and acts as a deep acceptor which can make the crystal insulating. Four different Zn-related centers have been by now identified, leading to light emission in the range between 1.8 eV and 2.9 eV. We present a first-principles investigation total energy and electronic structure calculations for Ga-substitutional and hetero-antisite N-substitutional Zn in wurtzite GaN, using ultrasoft pseudopotentials and a conjugate-gradient total energy minimization method. Our results permit the identification of the blue-light emission center as the substitutional acceptor, while contrary to a common belief the Zn_N heteroantisite has a very high formation energy and donor behavior, which seems to exclude it as the origin of the other centers.

1. Introduction

Wide-band-gap nitride semiconductors are promising material for the fabrication of blue-light emitting diode lasers. As-grown GaN is commonly found to be *n*-type conductive due to native donors;[1,2,3] Zn doping has been succesfully employed to obtain semi-insulating material.[4] There is general agreement that Zn is a very efficient donor compensator, that it introduces at least one deep acceptor level, and that it can act as recombination center. In recent works,[5,6] for moderate doping concentrations, only a single emission peaking at $\simeq 2.9$ eV has been detected in Zn-doped GaN. Other authors[7,8] report four luminescence bands peaking at 2.9, 2.6, 2.2 and 1.8 eV (referred to as bands A, B, C and D) at higher Zn concentrations. While the blue-light emission (band A) seems clearly related to a deep acceptor level of substitutional Zn, there is some debate about the origin of the other emission centers. Among the possible candidates, the most widely credited by the experimentalists are the acceptor levels originating from the various charge states with heteroantisite impurities Zn_N. Monemar *et al.*[7] suggest for the identity of levels B-D the charge states of Zn_N, namely Zn_N^-, Zn_N^{2-} and Zn_N^{3-}. Within this model, Zn_N should be able to bind up to three electrons with associated binding energies of 0.65, 1.02 and 1.43 eV.[7]

Recent theoretical investigations on native defects in GaN[9] have shown that the Ga_N antisite is a donor for a wide electron chemical potential range, and that its formation energy is so high as to allow only negligible concentrations in equilibrium conditions. In view of the similar electronic structure and atomic size of Ga and Zn, the behavior of the Zn heteroantisite should not be too different from that of the antisite proper; this points against the commonly accepted identification of levels B-D with Zn_N acceptor levels. Of course, a direct first-principles investigation may give important clues to confirm or refute this argument. Such calculation is provided in the present paper. Our calculations confirm that Zn_{Ga} is a single acceptor with a thermal ionization energy of 0.33 eV, and a recombination center with emission at 2.95 eV; further, they rule out the possibility that the B, C, and D emission bands may be related to $\mathrm{Zn_N}$, because of the high formation energy for this defect and of the gap level positions.

2. Method

Total energies and forces are calculated within local density functional theory, using a conjugate-gradient minimization scheme,[10] plane-waves, and ultrasoft pseudopotentials.[11] These allow for an accurate description of the localized Ga and Zn $3d$, and N $2p$ electrons using a cutoff of only 25 Ryd. Full defect geometry optimization is performed using a newly developed method (details given elsewhere), in 32-atom wurtzite GaN supercells. The formation energy of the defect in a charge state q is given by

$$E_f(q) = E^{tot}(q) - n^{\mathrm{Ga}}\mu^{\mathrm{Ga}} - n^{\mathrm{N}}\mu^{\mathrm{N}} - n^{\mathrm{Zn}}\mu^{\mathrm{Zn}} + qE_{\mathrm{F}}, \tag{1}$$

where $E^{tot}(q)$ is the defected supercell total energy in a specific charge state, E_{F} the electron chemical potential (the Fermi level), n^{Ga}, n^{N}, and n^{Zn} are the number of Ga, N, and Zn atoms, μ^{Ga}, μ^{N}, and μ^{Zn} their chemical potentials. These chemical potentials are not independent as they must satisfy the equilibrium conditions with GaN and $\mathrm{Zn_3N_2}$ compounds:

$$\mu^{\mathrm{GaN}} = \mu^{\mathrm{Ga}} + \mu^{\mathrm{N}}, \qquad \mu^{\mathrm{Zn_3N_2}} = 3\mu^{\mathrm{Zn}} + 2\mu^{\mathrm{N}}. \tag{2}$$

Using these relations and Eq. 1 we get

$$E_f(q) = E^{tot}(q) - n^{\mathrm{Ga}}\mu^{\mathrm{GaN}} - \frac{1}{3}\mu^{\mathrm{Zn_3N_2}} - \left(n^{\mathrm{N}} - n^{\mathrm{Ga}} - 2/3\right)\mu^{\mathrm{N}} + qE_{\mathrm{F}} \tag{3}$$

where μ^{N} is allowed to vary in the interval

$$\mu^{\mathrm{N_2}} \geq \mu^{\mathrm{N}} \geq \mu^{\mathrm{N_2}} + \frac{1}{2}\Delta H^{\mathrm{Zn_3N_2}} \tag{4}$$

Thus the degrees of freedom for the formation energy are reduced to one, the nitrogen chemical potential. It should be noted that in N-poor conditions the extremal value for μ^{N} is determined by the $\mathrm{Zn_3N_2}$ formation energy (1.28 eV) instead of that of GaN. This affects appreciably the formation energies of the substitutional and heteroantisite defect: the range of variation for the formation energy will be only 0.21 eV for $\mathrm{Zn_{Ga}}$, a much narrower range than in the case of native defects, and 1.06 for $\mathrm{Zn_N}$. All the chemical potentials are calculated ab initio with compatible technical ingredients.

3. Results and Discussion

In Table 1, we summarize the results for Zn, compared with data for the Mg and Ca acceptors (discussed elsewhere in these Proceedings). In Fig. 1 we display

Table 1. Zn impurities in wurtzite GaN. Formation energies E_f in N-rich and N-poor conditions, relaxation contribution to E_f, change in distance to neighbors in the *a*-plane (Δd_a) and along the *c*-axis (Δd_c) in percentage of the ideal bond lenght, are shown. All energies are in eV.

Defect	E_f N-rich	E_f N-poor	E_r	Δ d_a	Δ d_c
Zn_{Ga}^{-}	1.54	1.75	0.14	+1.1	+2.2
Zn_{Ga}^{0}	1.21	1.42	0.03	+1.1	−0.5
Zn_{N}^{2-}	13.15	12.09	2.64	+10.2	+9.3
Zn_{N}^{1-}	9.68	8.62	3.26	+13.0	+9.9
Zn_{N}^{0}	7.66	6.60	3.22	+11.7	+12.1
Zn_{N}^{1+}	5.44	4.38	4.09	+13.5	+17.0
Zn_{N}^{2+}	4.87	3.81	5.14	+16.1	+18.0
Mg_{Ga}^{0}	1.40	1.95	0.21	+3.2	+3.2
Ca_{Ga}^{0}	2.15	2.70	1.87	+10.0	+12.7

the defect formation energies vs. the Fermi energy in the N-rich case. The results for Zn_{Ga} confirm the identification of this defect with the blue-light recombination center. Zn_{Ga} is a single acceptor with a thermal ionization energy of 0.33 eV, in good agreement with the existing experimental data. The calculated formation energy for Zn_{Ga}^{0} is quite low, which is compatible with the high Zn doping concentrations achievable in GaN. Such a low formation cost matches the size similarities of the Zn and Ga atoms. Zn is able to occupy the substitutional site in the GaN lattice without inducing a significant distortion; Mg, and especially Ca, have a bigger atomic radius and their incorporation causes sizable relaxations. Increasing atomic size mismatch correlates (see Table 1) with increasing relaxation energy and formation energy.

We found the Frank-Condon shift for Zn_{Ga}^{-}/Zn_{Ga}^{0} to be 0.12 eV (very close to the difference of the relaxation energies of the two states). Adding this to the thermal binding energy gives 0.45 eV for the optical ionization level. This is in remarkable agreement with the experimental luminescence emission energy for band A of 2.9 eV which (using the experimental value of 3.4 eV for the GaN gap) yields an optical level at 0.5 eV above the valence band top. In Fig. 2 we plot the electronic density of the highest occupied state of the Zn_{Ga}^{-} defect along the atomic chains in the $(\bar{1}2\bar{1}0)$ plane. It is clear that the level is mainly of N $p_{xy}-$like character, with Zn $3d$ admixture, while components from N p_z and Ga are negligible. This feature is peculiar of *wurtzite* GaN, whose highest valence band is a N p_{xy} doublet laying in the *a*-plane.

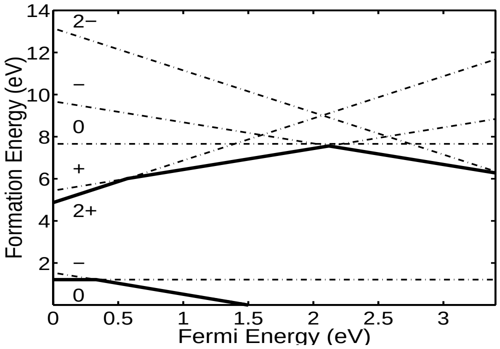

Fig. 1: Defect formation energy vs. Fermi energy E_F, referred to the valence band top.

For the Zn heteroantisite, the formation energy is very high. This rules out the possibility of having appreciable concentration of this defect in equilibrium conditions. Further, we find only two ionization levels in the gap, $\epsilon(2+/+) = 0.57$ eV and $\epsilon(+/-) = 2.22$ eV. The doubly and singly positive, and singly negative states are then the only ones permitted; note the negative-U behavior causing the instability of the neutral charge state. This in contrast with the three levels (–,2–,3–) needed to explain the B, C, and D emission bands. The large formation energy is related to the large atomic size mismatch between N and Zn. A strong outward relaxation occurs at the defect, of a magnitude comparable with that reported for the Ga antisite.[9] We mention further that preliminary results on the formation energy of interstitial Zn indicate that this center should be present in very low concentrations only, and cannot be responsible for the observed emission bands. Further interesting preliminary results are available on Cd. The thermal ionization energy is 0.65, and the optical level is 0.79 eV. Cd therefore lends itself as a recombination center at around 2.6 eV. This may be of use in yellow-green emitters based on InGaN alloys, where a lower In mole fraction may be needed, with ensuing improved material quality. Cd_N heteroantisites behave similarly to Zn_N, and are therefore irrelevant.

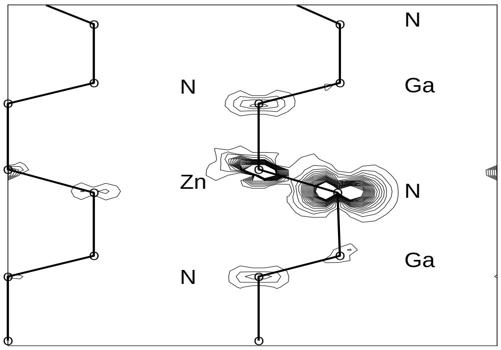

Fig. 2: Electronic density for the highest occupied state of Zn_{Ga}^{-} defect.

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